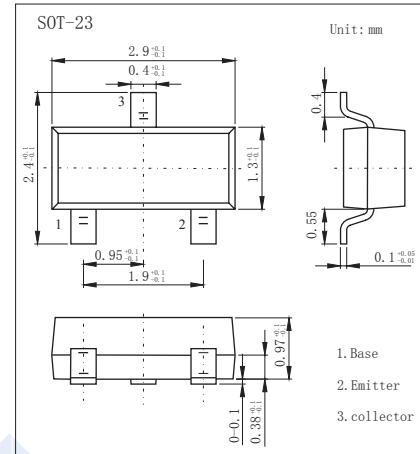


NPN Transistors

2SC3324

■ Features

- Collector Current Capability $I_c=100\text{mA}$
- Collector Emitter Voltage $V_{CE0}=120\text{V}$
- Complementary to 2SA1312

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	120	V
Collector - Emitter Voltage	V_{CE0}	120	
Emitter - Base Voltage	V_{EB0}	5	
Collector Current - Continuous	I_c	100	mA
Base Current	I_B	20	
Collector Power Dissipation	P_c	150	mW
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 125	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_c = 100 \mu\text{A}, I_E = 0$	120			V
Collector- emitter breakdown voltage	V_{CE0}	$I_c = 1 \text{ mA}, I_B = 0$	120			
Emitter - base breakdown voltage	V_{EB0}	$I_E = 100 \mu\text{A}, I_c = 0$	5			
Collector-base cut-off current	I_{CB0}	$V_{CB} = 120\text{V}, I_E = 0$			0.1	uA
Emitter cut-off current	I_{EB0}	$V_{EB} = 5\text{V}, I_c = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = 10 \text{ mA}, I_B = 1 \text{ mA}$			0.3	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = 10 \text{ mA}, I_B = 1 \text{ mA}$			1.2	
DC current gain	h_{FE}	$V_{CE} = 6\text{V}, I_c = 2 \text{ mA}$	200		700	
Noise figure	NF	$V_{CE} = 6\text{V}, I_c = 0.1 \text{ mA}, f = 100 \text{ Hz}, R_G = 10 \text{ K}\Omega$			6	dB
		$V_{CE} = 6\text{V}, I_c = 0.1 \text{ mA}, f = 1 \text{ KHz}, R_G = 10 \text{ K}\Omega$			3	
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1 \text{ MHz}$		4		pF
Transition frequency	f_T	$V_{CE} = 6\text{V}, I_c = 1 \text{ mA}$		100		MHz

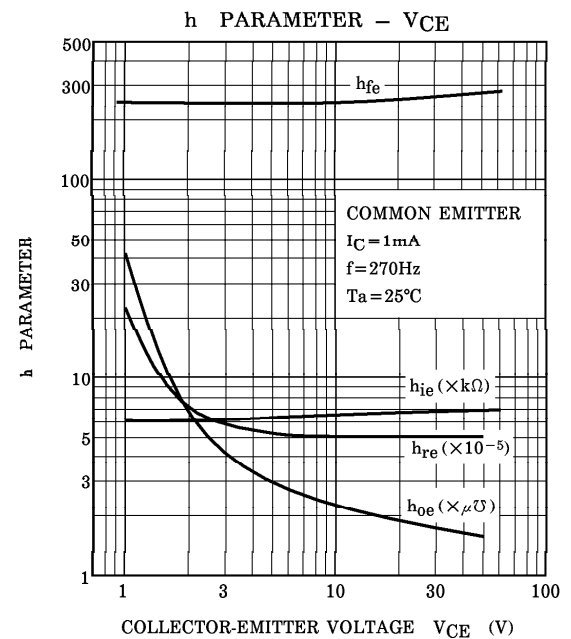
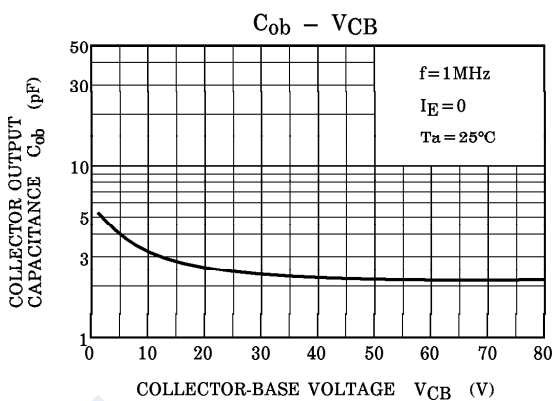
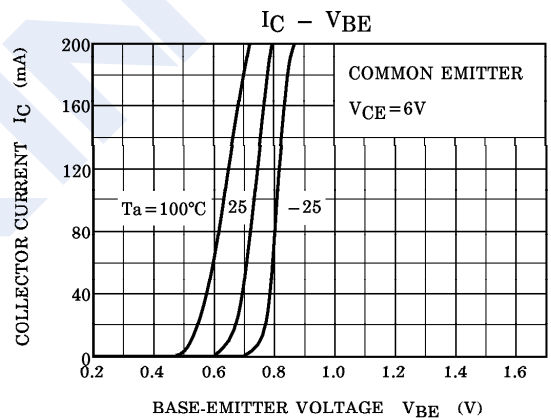
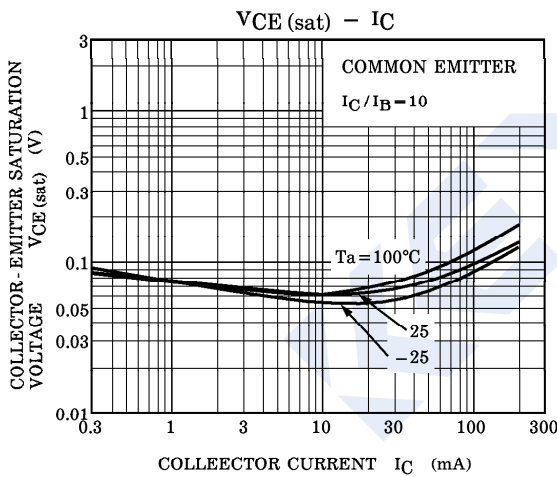
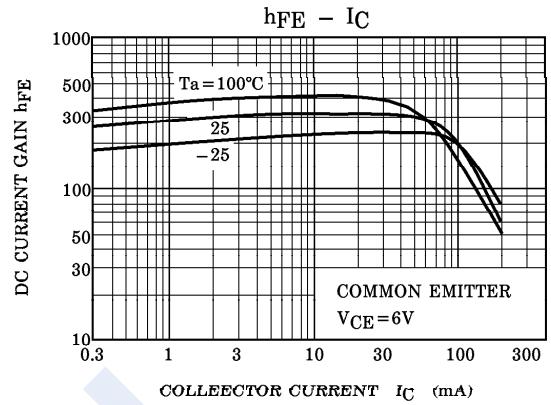
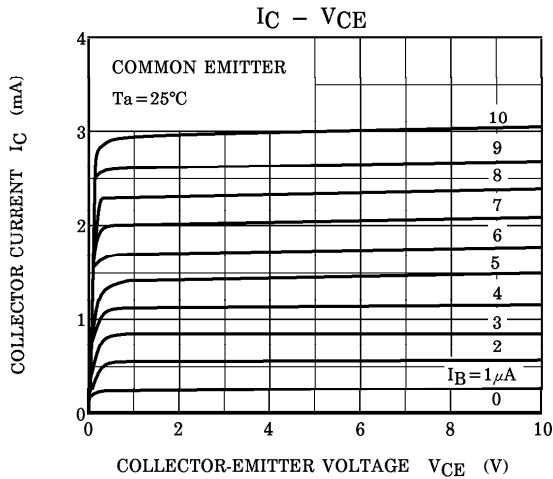
■ Classification of h_{FE}

Type	2SC3324-G	2SC3324-L
Range	200-400	350-700
Marking	CB G	CB L

NPN Transistors

2SC3324

■ Typical Characteristics



NPN Transistors

2SC3324

■ Typical Characteristics

